

# 9<sup>th</sup> International Workshop on Compact Modeling

January 30 (Mon.), 2012

Sydney, Australia

	Title	Authors	Affiliation
9:20-9:30	Opening: Jin He ( chair)		
	<b>Simulation Technique and Methodology</b>		
9:30-9:50	1 I-MOS.org – Interactive Modeling and Online Simulation Platform for Compact Modeling	Hao Wang et al.	Hong Kong University of Science and Technology
9:50-10:10	2 A Study on the Effects of the Extended Nitride Length in the Charge Trap Flash Memory using a Self-Consistent Simulation	Sang Yong Park et al.	Seoul National University
10:10-10:30	3 A Nonlinear Poisson- Schrodinger Solver under Cylindrical Coordinate for Quantum Effect in Nanowire MOSFET	Lining Zhang et al.	Peking University
10:30-10:40	-Break-		
	<b>Tunneling Device Modeling</b>		
10:40-11:00	4 A Physics-Based Compact Model for Gate-All-Around Si Nanowire Tunneling FETs (GAA NW-tFETs)	Ling Li et al.	Tsinghua University
11:00-11:20	5 Predicting Key Features of Double-Gate Tunnel FETs	Lining Zhang et al.	Hong Kong University of Science and Technology
11:30-13:30	- Lunch Break-		
	<b>Transient Effect Modeling</b>		
14:30-14:50	6 Reverse-Recovery-Effect Modeling for p-i-n Diodes	M. Miyake et al.	Horishama University
14:50-15:10	7 Transient History-Effect in SOI-MOSFETs and its Compact Modeling	A. Toda et al.	Hiroshima University
	<b>Reliability Modeling and Simulation</b>		
15:10-15:30	8 Stochastic Simulation of the NBTI and FN Relaxation using the 3D Monte Carlo Method	Seongwook et al	Seoul National University
15:30-15:50	9 Vertical Nonuniformity Effect on FinFET Performance Characteristics	Wei Bian et al	Hong Kong University of Science and Technology
15:50-16:10	10 Analytic Model for Threshold Voltage Instability of MOSFETs with High K Gate Stack	Jin He et al	Peking University
16:10-16:20	Closing: H.J.Mattausch		